L Number	Hits	Search Text	DB	Time stamp
1	126572	(semiconductor$1 chip$1 die dice$1 ic$2 integrated adj circuit$1) and (heat thermal$2) near3 (sink$3 absorb$3 dissipat$3 exchang$3 remov$3 transfer$4)	USPAT; US-PGPUB; EPO; JPO	2004/02/08 16:45
2	7795	((semiconductor$1 chip$1 die dice$1 ic$2 integrated adj circuit$1) and (heat thermal$2) near3 (sink$3 absorb$3 dissipat$3 exchang$3 remov$3 transfer$4)) and (heat thermal$2) near3 (sink$3 absorb$3 dissipat$3 exchang$3 remov$3 transfer$4) same (carbon$6 graphit$2 diamon)	USPAT; US-PGPUB; EPO; JPO	2004/02/08 16:47
3	1039	((semiconductor$1 chip$1 die dice$1 ic$2 integrated adj circuit$1) and (heat thermal$2) near3 (sink$3 absorb$3 dissipat$3 exchang$3 remov$3 transfer$4)) and solder$3 same (carbon$6 graphit$2 diamond)	USPAT; US-PGPUB; EPO; JPO	2004/02/08 16:48
4	34	(((semiconductor$1 chip$1 die dice$1 ic$2 integrated adj circuit$1) and (heat thermal$2) near3 (sink$3 absorb$3 dissipat$3 exchang$3 remov$3 transfer$4)) and solder$3 same (carbon$6 graphit$2 diamond)) and solder$3 same (carbon$6 graphit$2 diamond) same (foam por$3 porosit$3)	USPAT; US-PGPUB; EPO; JPO	2004/02/08 16:48
5	34	((((semiconductor$1 chip$1 die dice$1 ic$2 integrated adj circuit$1) and (heat thermal$2) near3 (sink$3 absorb$3 dissipat$3 exchang$3 remov$3 transfer$4)) and solder$3 same (carbon$6 graphit$2 diamond)) and solder$3 same (carbon$6 graphit$2 diamond) same (foam por$3 porosit$3)) and solder$3 same (carbon$6 graphit$2 diamond)	USPAT; US-PGPUB; EPO; JPO	2004/02/08 17:53
6	0	("wo27776").PN.	USPAT; US-PGPUB; EPO; JPO	2004/02/08 17:53